



N-Channel 60-V (D-S) MOSFET

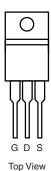
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)	
60	0.012 at V _{GS} = 10 V	60 ^d	33	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



TO-220AB

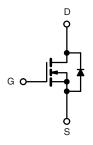


Ordering Information: SUP60N06-12P-E3 (Lead (Pb)-free)

SUP60N06-12P-GE3 (Lead (Pb)-free and Halogen-free)

APPLICATIONS

- Synchronous Rectifier
- **Power Supplies**



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V_{DS}	60	V			
Gate-Source Voltage		V _{GS}	± 20			
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 25 °C	I-	60 ^d			
Continuous Diam Current (1) = 130 C)	T _C = 70 °C	l _D	54 ^d	A		
Pulsed Drain Current		I _{DM}	80			
Avalanche Current		I _{AS}	40			
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	80	mJ		
Mariana Paran Pinain ation?	T _C = 25 °C	P _D	100 ^b	W		
Maximum Power Dissipation ^a	T _A = 25 °C ^c	'-D	3.25	VV		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)	R _{thJC}	1.25		

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When Mounted on 1" square PCB (FR-4 material).
- d. Package limited.

SUP60N06-12P

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	60			V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.5		4.5	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA
Zero Gate Voltage Drain Current		V _{DS} = 60 V, V _{GS} = 0 V			1	
	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 150 ^{\circ}\text{C}$			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	80			Α
Drain-Source On-State Resistance ^a	Б	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$		0.0098	0.012	Ω
	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}, T_J = 125 ^{\circ}\text{C}$		0.0155	0.019	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		37		S
Dynamic ^b				•		
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 30 V, f = 1 MHz		1970		pF
Output Capacitance	C _{oss}			310		
Reverse Transfer Capacitance	C _{rss}			110		
Total Gate Charge ^c	Q_g			33	55	nC
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		11		
Gate-Drain Charge ^c	Q_{gd}			9		
Gate Resistance	R_{g}	f = 1 MHz	0.3	1.4	2.8	Ω
Turn-On Delay Time ^c	t _{d(on)}			11	20	
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 1.53 Ω		11	20	ns
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		16	30	
Fall Time ^c	t _f			8	15	
Source-Drain Diode Ratings and Cha	aracteristics T	_C = 25 °C ^b				
Continuous Current	I _S				60	
Pulsed Current	I _{SM}				80	Α
Forward Voltage ^a	V _{SD}	I _F = 10 A, V _{GS} = 0 V		0.84	1.5	٧
Reverse Recovery Time	t _{rr}			40	80	ns
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = 10 A, dl/dt = 100 A/μs		3.2	5.0	Α
Reverse Recovery Charge	Q _{rr}			64	120	nC

Notes:

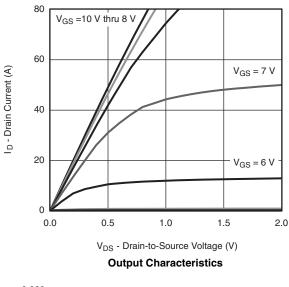
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

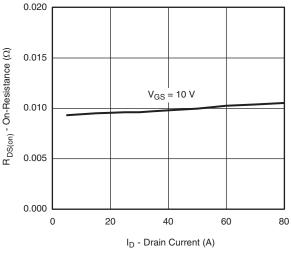
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



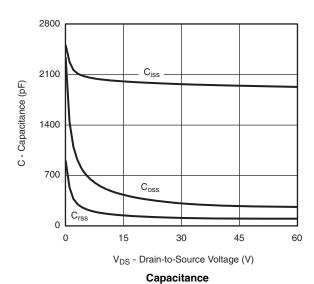


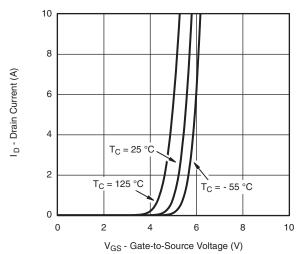
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



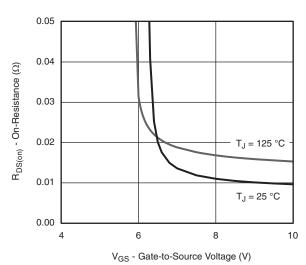


On-Resistance vs. Drain Current

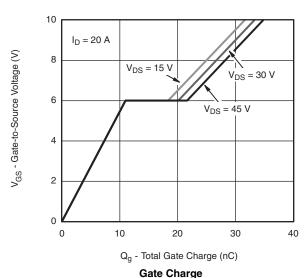




Transfer Characteristics



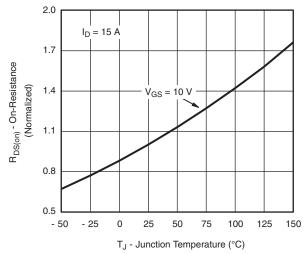
On-resistance vs. Gate-to-Source Voltage



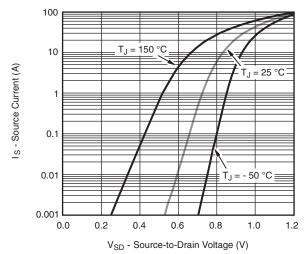
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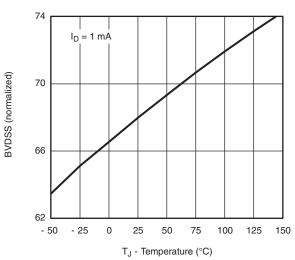
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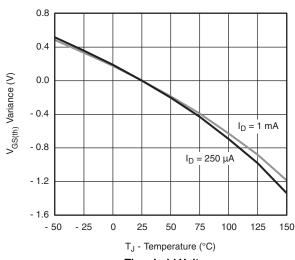
On-Resistance vs. Junction Temperature



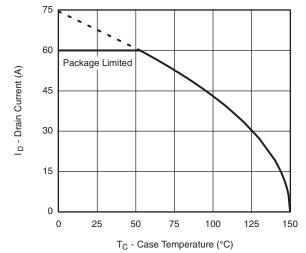
Source-Drain Diode Forward Voltage



Drain-Source Breakdown vs. Junction Temperature



Threshold Voltage

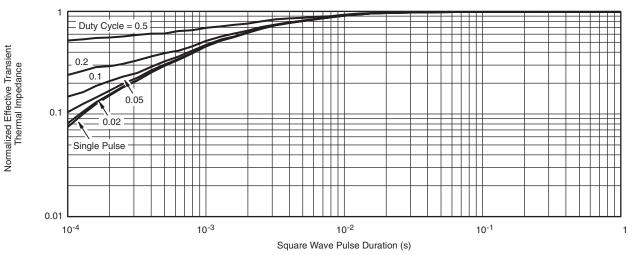


Maximum Drain Current vs. Case Temperature



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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